PROCESS CP794R

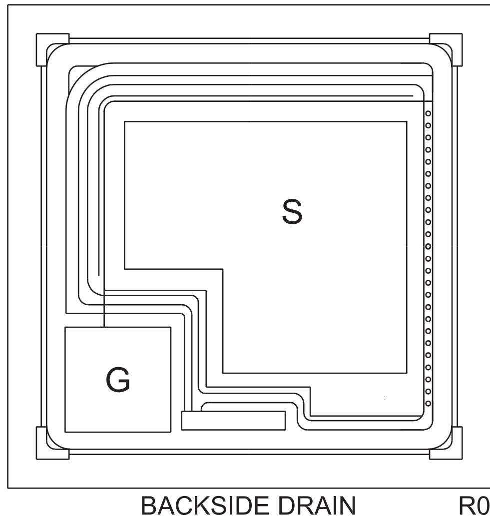
Small Signal MOSFET Transistor

P - Channel Enhancement-Mode Transistor Chip

PROCESS DETAILS

Die Size	15.7 x 15.7 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	9.1 x 8.1 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE DRAIN R0

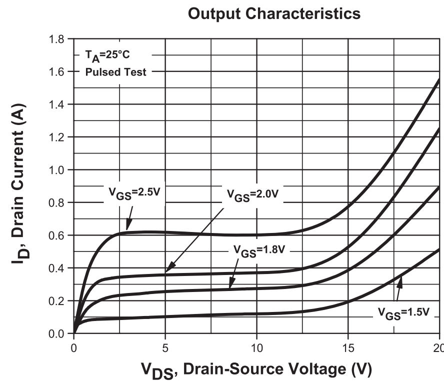
GROSS DIE PER 6 INCH WAFER
95,400

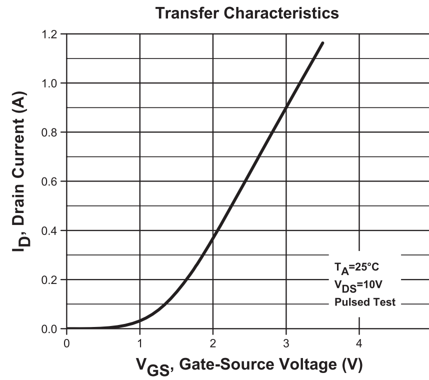
PRINCIPAL DEVICE TYPES
CEDM8004
CMLM0584
CMLDM7484

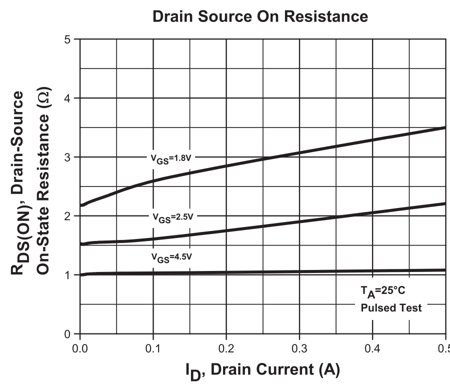
R0 (29-July 2010)

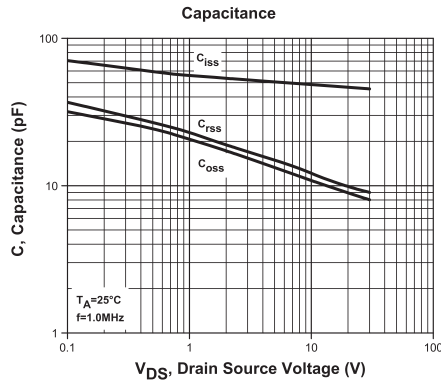
PROCESS CP794R

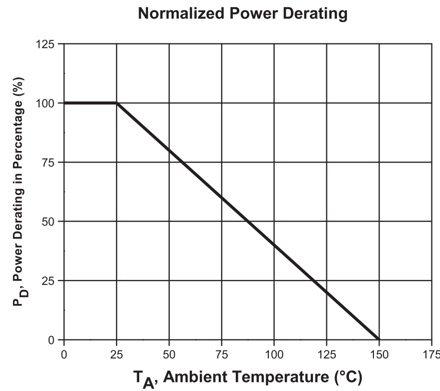
Typical Electrical Characteristics











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